

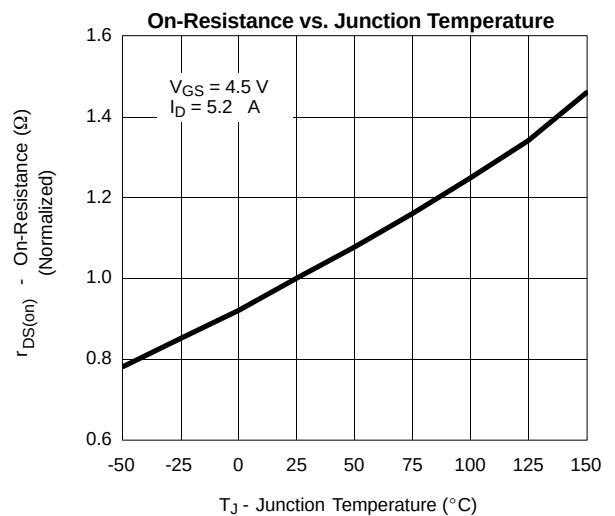
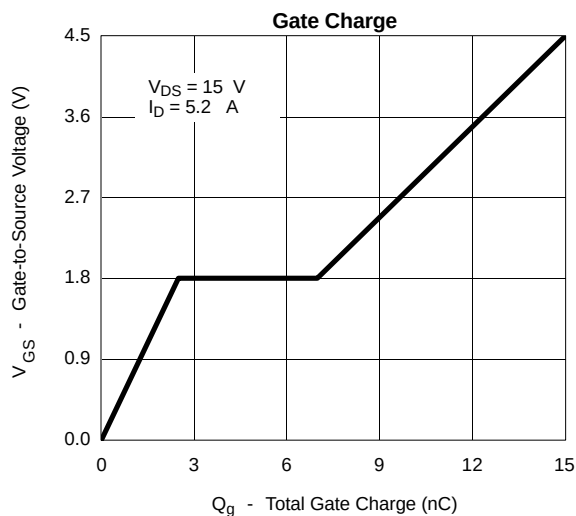
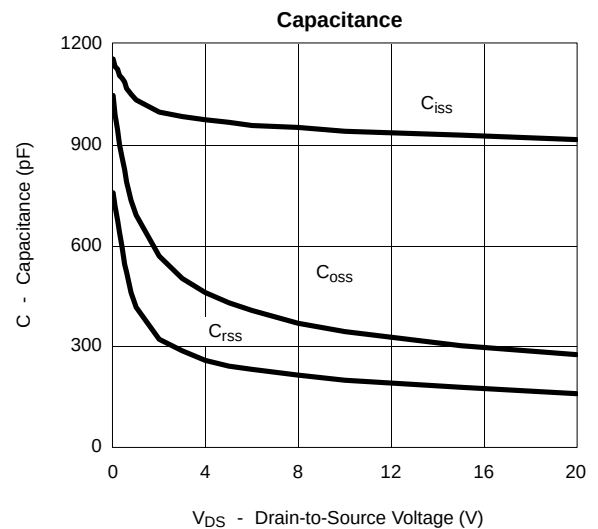
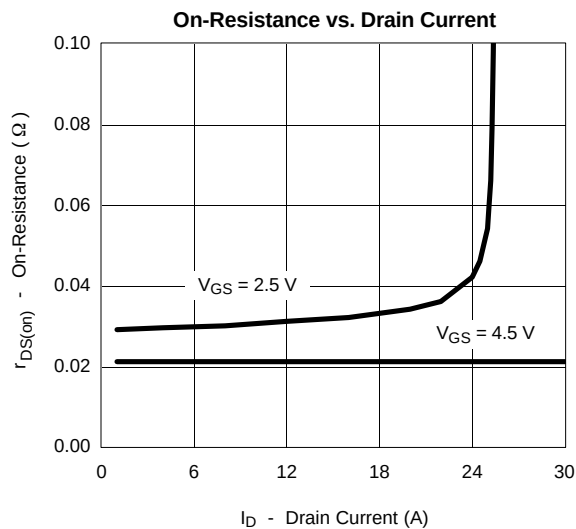
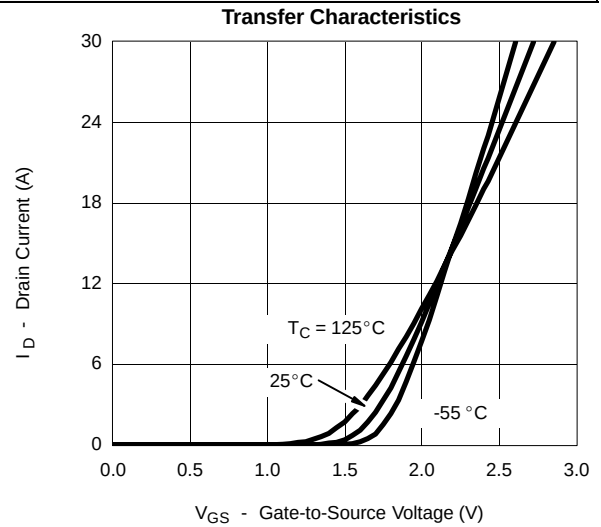
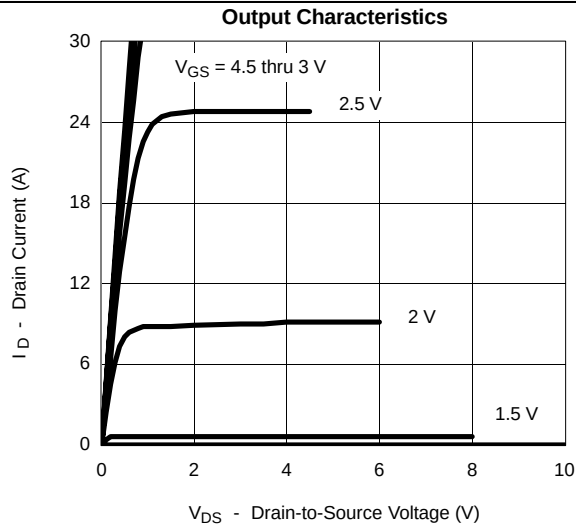
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = +20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			25	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 5.2 A		0.021	0.030	Ω
		V _{GS} = 2.5 V, I _D = 4.5 A		0.028	0.040	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 5.2 A		20		S
Diode Forward Voltage ^a	V _{SD}	I _S = 1.25 A, V _{GS} = 0 V		0.65	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5.2 A		15	25	nC
Gate-Source Charge	Q _{gs}			2.5		
Gate-Drain Charge	Q _{gd}			4.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 10 Ω I _D ≈ 1 A, V _{GEN} = 4.5 V, R _G = 6 Ω		100	200	ns
Rise Time	t _r			130	250	
Turn-Off Delay Time	t _{d(off)}			420	800	
Fall Time	t _f			220	450	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.25 A, di/dt = 100 A/μs		210	500	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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